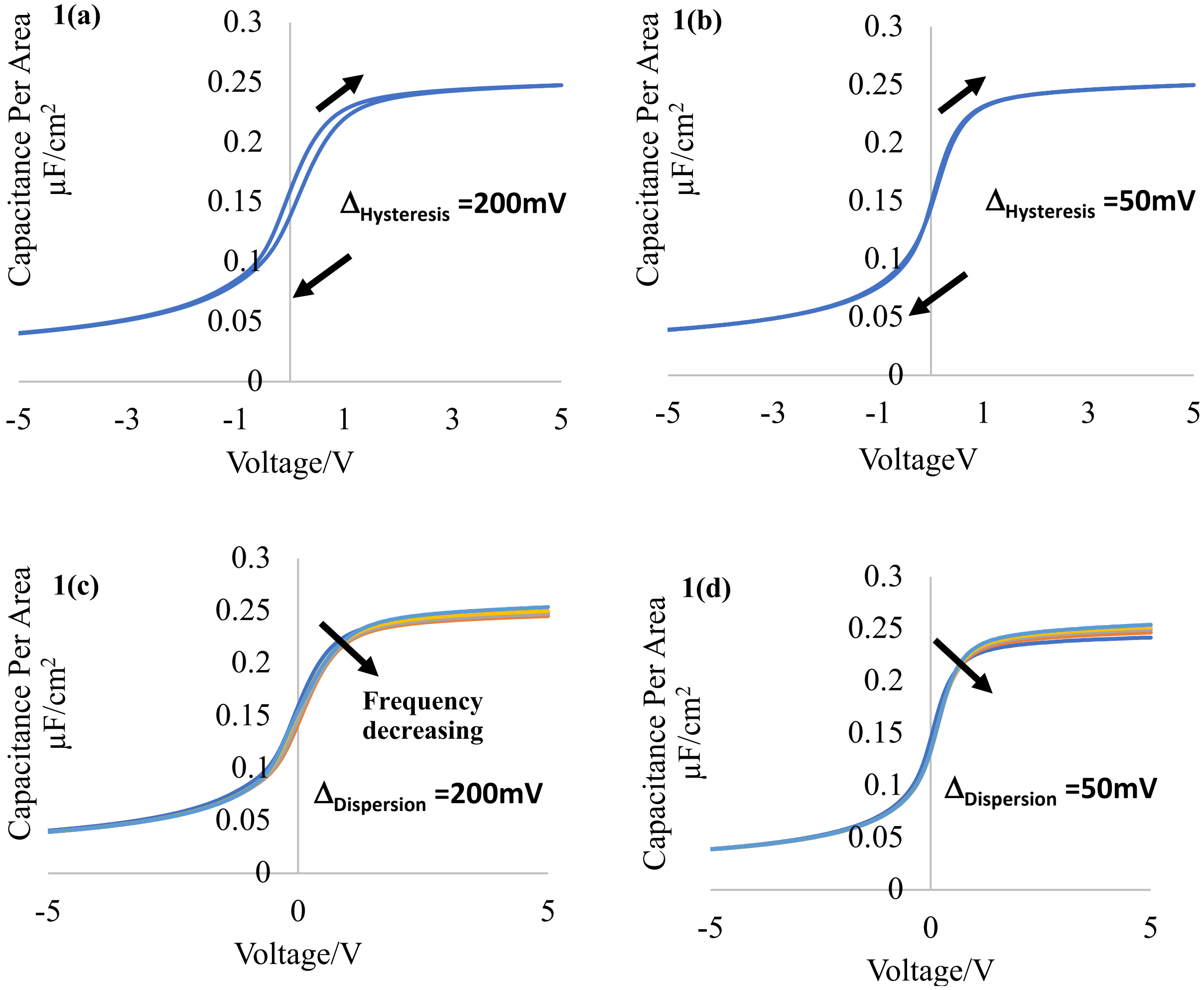

Figure 1 (a)Hysteresis of GaN MOSCAPs with 20nm Al_2O_3 gate dielectric, (b)Hysteresis of GaN MOSCAPs with 2nm AlN/20nm Al_2O_3 gate stack, (c)Frequency dispersion of GaN MOSCAPs with 20nm Al_2O_3 gate dielectric and (d)Frequency dispersion of GaN MOSCAPs with 2nm AlN/20nm Al_2O_3 gate stack

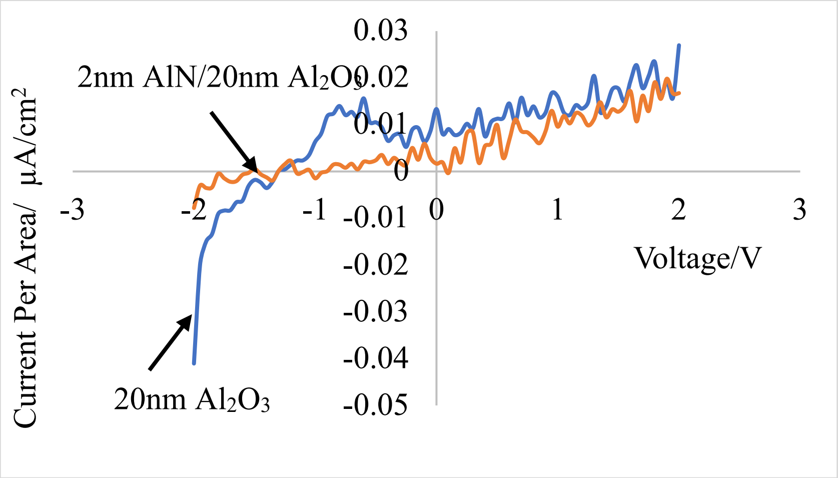

Figure 2: Comparative leakage currents of GaN MOSCAPs with 20 nm Al_2O_3 and 2nm AlN/20nm Al_2O_3 gate stacks